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Dual 4-input NAND gate Rev. 1 — 17 July 2012

Product data sheet

1. **General description**

The 74HC20-Q100; 74HCT20-Q100 is a dual 4-input NAND gate. Inputs include clamp diodes. This enables the use of current limiting resistors to interface inputs to voltages in excess of V_{CC}.

This product has been qualified to the Automotive Electronics Council (AEC) standard Q100 (Grade 1) and is suitable for use in automotive applications.

2. Features and benefits

- Automotive product qualification in accordance with AEC-Q100 (Grade 1)
 - Specified from –40 °C to +85 °C and from –40 °C to +125 °C
- Complies with JEDEC standard JESD7A
- Low-power dissipation
- Input levels:
 - For 74HC20-Q100: CMOS level
 - For 74HCT20-Q100: TTL level
- ESD protection:
 - MIL-STD-883, method 3015 exceeds 2000 V
 - HBM JESD22-A114F exceeds 2000 V
 - MM JESD22-A115-A exceeds 200 V (C = 200 pF, R = 0 Ω)
- Multiple package options

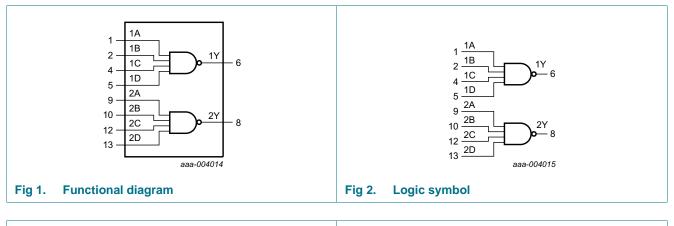
Ordering information 3.

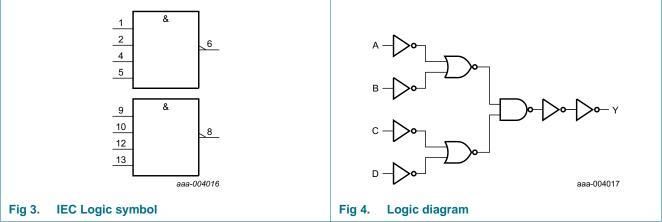
Type number	Package						
	Temperature range	Name	Description	Version			
74HC20D-Q100	–40 °C to +125 °C	SO14	plastic small outline package; 14 leads; body width	SOT108-1			
74HCT20D-Q100			3.9 mm				
74HC20PW-Q100	–40 °C to +125 °C	TSSOP14	plastic thin shrink small outline package; 14 leads; body width 4.4 mm	SOT402-1			



Dual 4-input NAND gate

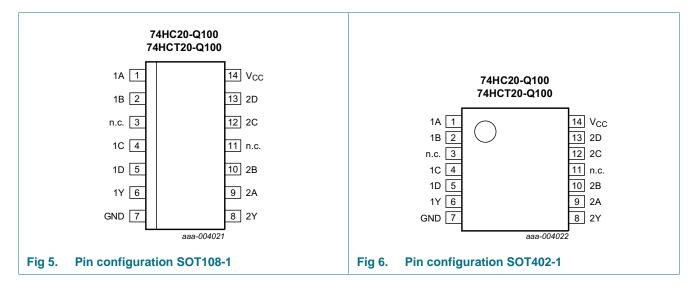
4. Functional diagram





5. Pinning information

5.1 Pinning



Dual 4-input NAND gate

5.2 Pin description

Table 2.Pin description		
Symbol	Pin	Description
1A, 1B, 1C, 1D	1, 2, 4, 5	data input
n.c.	3, 11	not connected
1Y	6	data output
GND	7	ground (0 V)
2Y	8	data output
2A, 2B, 2C, 2D	9, 10, 12, 13	data input
V _{CC}	14	supply voltage

6. Functional description

Table 3. Function table^[1]

Input				Output
nA	nB	nC	nD	nY
L	Х	Х	Х	Н
Х	L	Х	Х	Н
Х	Х	L	Х	Н
Х	Х	Х	L	Н
Н	Н	Н	Н	L

[1] H = HIGH voltage level; L = LOW voltage level; X = don't care.

7. Limiting values

Table 4.Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

		331		10	,
Symbol	Parameter	Conditions	Min	Max	Unit
V _{CC}	supply voltage		-0.5	+7	V
I _{IK}	input clamping current	V_{I} < -0.5 V or V_{I} > V_{CC} + 0.5 V	<u>[1]</u> -	±20	mA
I _{OK}	output clamping current	$V_{\rm O}$ < –0.5 V or $V_{\rm O}$ > $V_{\rm CC}$ + 0.5 V	<u>[1]</u> _	±20	mA
lo	output current	$-0.5 \text{ V} < \text{V}_{\text{O}} < \text{V}_{\text{CC}} + 0.5 \text{ V}$	-	±25	mA
I _{CC}	supply current		-	50	mA
I _{GND}	ground current		-50	-	mA
T _{stg}	storage temperature		-65	+150	°C
P _{tot}	total power dissipation		[2] _	500	mW
-					

[1] The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

[2] For SO14 package: P_{tot} derates linearly with 8 mW/K above 70 $^\circ\text{C}.$

For SSOP14 packages: Ptot derates linearly with 5.5 mW/K above 60 °C.

Dual 4-input NAND gate

8. Recommended operating conditions

Table 5. Recommended operating conditions

Voltages are referenced to GND (ground = 0 V)

Symbol	Parameter	Conditions	74HC20-Q100			74HCT20-Q100			Unit
			Min	Тур	Max	Min	Тур	Max	
V _{CC}	supply voltage		2.0	5.0	6.0	4.5	5.0	5.5	V
VI	input voltage		0	-	V _{CC}	0	-	V_{CC}	V
Vo	output voltage		0	-	V _{CC}	0	-	V_{CC}	V
T _{amb}	ambient temperature		-40	+25	+125	-40	+25	+125	°C
$\Delta t / \Delta V$	input transition rise and fall rate	$V_{CC} = 2.0 V$	-	-	625	-	-	-	ns/V
		$V_{CC} = 4.5 V$	-	1.67	139	-	1.67	139	ns/V
		$V_{CC} = 6.0 V$	-	-	83	-	-	-	ns/V

9. Static characteristics

Table 6. Static characteristics

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions		25 °C		–40 °C t	o +85 °C	–40 °C to	o +125 ℃	Unit
			Min	Тур	Max	Min	Max	Min	Max	
74HC20	-Q100								1	
V _{IH}	HIGH-level	$V_{CC} = 2.0 V$	1.5	1.2	-	1.5	-	1.5	-	V
	input voltage	$V_{CC} = 4.5 V$	3.15	2.4	-	3.15	-	3.15	-	V
		$V_{CC} = 6.0 V$	4.2	3.2	-	4.2	-	4.2	-	V
V _{IL}	LOW-level	$V_{CC} = 2.0 V$	-	0.8	0.5	-	0.5	-	0.5	V
	input voltage	$V_{CC} = 4.5 V$	-	2.1	1.35	-	1.35	-	1.35	V
		$V_{CC} = 6.0 V$	-	2.8	1.8	-	1.8	-	1.8	V
V _{ОН}	HIGH-level	$V_{I} = V_{IH} \text{ or } V_{IL}$								
	output voltage	$I_{O} = -20 \ \mu A; \ V_{CC} = 2.0 \ V$	1.9	2.0	-	1.9	-	1.9	-	V
		I_{O} = -20 μ A; V_{CC} = 4.5 V	4.4	4.5	-	4.4	-	4.4	-	V
		$I_O = -20 \ \mu A; \ V_{CC} = 6.0 \ V$	5.9	6.0	-	5.9	-	5.9	-	V
		I_{O} = -4.0 mA; V_{CC} = 4.5 V	3.98	4.32	-	3.84	-	3.7	-	V
		I_{O} = -5.2 mA; V_{CC} = 6.0 V	5.48	5.81	-	5.34	-	5.2	-	V
V _{OL}	LOW-level	$V_{I} = V_{IH} \text{ or } V_{IL}$								
	output voltage	$I_O = 20 \ \mu\text{A}; \ V_{CC} = 2.0 \ \text{V}$	-	0	0.1	-	0.1	-	0.1	V
		$I_O = 20 \ \mu\text{A}; \ V_{CC} = 4.5 \ \text{V}$	-	0	0.1	-	0.1	-	0.1	V
		$I_0 = 20 \ \mu A; \ V_{CC} = 6.0 \ V$	-	0	0.1	-	0.1	-	0.1	V
		I_{O} = 4.0 mA; V_{CC} = 4.5 V	-	0.15	0.26	-	0.33	-	0.4	V
		I_{O} = 5.2 mA; V_{CC} = 6.0 V	-	0.16	0.26	-	0.33	-	0.4	V
1	input leakage current	$V_I = V_{CC} \text{ or GND};$ $V_{CC} = 6.0 \text{ V}$	-	-	±0.1	-	±1	-	±1	μΑ
I _{CC}	supply current		-	-	2	-	20	-	40	μΑ

Dual 4-input NAND gate

Symbol	Parameter	Conditions		25 °C		–40 °C t	o +85 °C	–40 °C to	o +125 °C	Unit
			Min	Тур	Max	Min	Max	Min	Max	
Cı	input capacitance		-	3.5	-	-	-	-	-	pF
74HCT2	0-Q100									
V _{IH}	HIGH-level input voltage	V_{CC} = 4.5 V to 5.5 V	2.0	1.6	-	2.0	-	2.0	-	V
VIL	LOW-level input voltage	V_{CC} = 4.5 V to 5.5 V	-	1.2	0.8	-	0.8	-	0.8	V
V _{OH} HIGH-level		$V_{I} = V_{IH} \text{ or } V_{IL}; V_{CC} = 4.5 \text{ V}$								
	output voltage	I _O = -20 μA	4.4	4.5	-	4.4	-	4.4	-	V
		$I_{O} = -4.0 \text{ mA}$	3.98	4.32	-	3.84	-	3.7	-	V
V _{OL}	LOW-level	$V_{I} = V_{IH} \text{ or } V_{IL}; V_{CC} = 4.5 \text{ V}$								
	output voltage	I _O = 20 μA	-	0	0.1	-	0.1	-	0.1	V
		I _O = 5.2 mA	-	0.15	0.26	-	0.33	-	0.4	V
lı	input leakage current	$V_I = V_{CC}$ or GND; $V_{CC} = 5.5 V$	-	-	±0.1	-	±1	-	±1	μA
I _{CC}	supply current	$\label{eq:VI} \begin{array}{l} V_{I} = V_{CC} \text{ or } GND; \ I_{O} = 0 \ A; \\ V_{CC} = 5.5 \ V \end{array}$	-	-	2	-	20	-	40	μA
ΔI _{CC}	additional supply current	per input pin; $V_I = V_{CC} - 2.1 \text{ V}; I_O = 0 \text{ A};$ other inputs at V_{CC} or GND; $V_{CC} = 4.5 \text{ V}$ to 5.5 V	-	30	108	-	135	-	147	μA
CI	input capacitance		-	3.5	-	-	-	-	-	pF

Table 6. Static characteristics ...continued

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

74HC_HCT20_Q100
Product data sheet

Table 7

74HC20-Q100; 74HCT20-Q100

Dual 4-input NAND gate

10. Dynamic characteristics

Dynamic characteristics

Symbol	Parameter	Conditions		25 °C		–40 °C to	o +125 °C	Unit	
		-		Min	Тур	Max	Max (85 °C)	Max (125 °C)	
74HC20-	Q100								
t _{pd}	propagation delay	nA, nB, nC or nD to nY; see <u>Figure 7</u>	<u>[1]</u>						
		$V_{CC} = 2.0 V$		-	28	90	115	135	ns
	$V_{CC} = 4.5 V$		-	10	18	23	27	ns	
		$V_{CC} = 6.0 V$		-	8	15	20	23	ns
		$V_{CC} = 5.0 \text{ V}; \text{ C}_{L} = 15 \text{ pF}$		-	8	-	-	-	ns
t _t tra	transition time	see Figure 7	[2]						
		$V_{CC} = 2.0 V$		-	19	75	95	110	ns
		$V_{CC} = 4.5 V$		-	7	15	19	22	ns
		$V_{CC} = 6.0 V$		-	6	13	16	19	ns
C _{PD}	power dissipation capacitance	per package; $V_1 = GND$ to V_{CC}	<u>[3]</u>	-	22	-	-	-	pF
74HCT2	0-Q100								
t _{pd}	propagation delay	nA, nB, nC or nD to nY; see <mark>Figure 7</mark>	<u>[1]</u>						
		$V_{CC} = 4.5 V$		-	16	28	35	42	ns
		$V_{CC} = 5.0 \text{ V}; \text{ C}_{L} = 15 \text{ pF}$		-	13	-	-	-	ns
t _t	transition time	V_{CC} = 4.5 V; see <u>Figure 7</u>	[2]	-	7	15	19	22	ns
C _{PD}	power dissipation capacitance	per package; V _I = GND to V _{CC} – 1.5 V	<u>[3]</u>	-	17	-	-	-	pF

[1] t_{pd} is the same as t_{PHL} and t_{PLH} .

 $\label{eq:ttilde} [2] \quad t_t \mbox{ is the same as } t_{THL} \mbox{ and } t_{TLH}.$

[3] C_{PD} is used to determine the dynamic power dissipation (P_D in μ W):

 $P_D = C_{PD} \times V_{CC}^2 \times f_i \times N + \sum (C_L \times V_{CC}^2 \times f_o)$ where:

 f_i = input frequency in MHz;

 $f_o = output frequency in MHz;$

 C_L = output load capacitance in pF;

 V_{CC} = supply voltage in V;

N = number of inputs switching;

 $\Sigma~(C_L \times V_{CC}{}^2 \times f_o)$ = sum of outputs.

Dual 4-input NAND gate

11. Waveforms

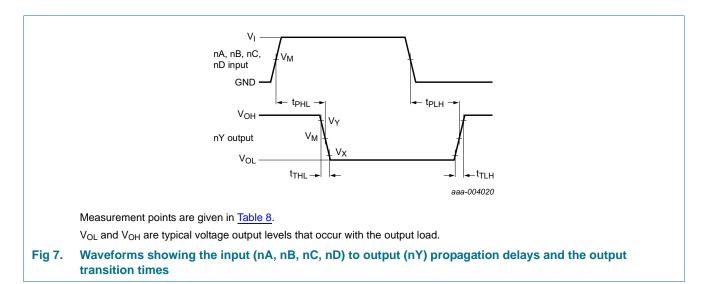
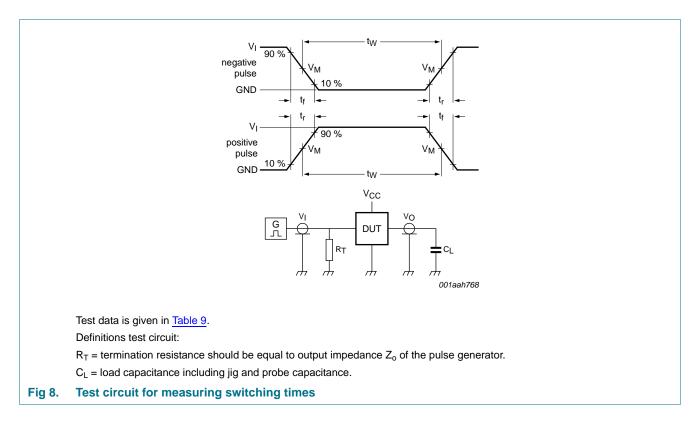


Table 8. Measurement points

Туре	Input	Output	Output			
	V _M	V _M	V _X	V _Y		
74HC20-Q100	0.5V _{CC}	0.5V _{CC}	0.1V _{CC}	0.9V _{CC}		
74HCT20-Q100	1.3 V	1.3 V	0.1V _{CC}	0.9V _{CC}		



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74HC_HCT20_Q100

Dual 4-input NAND gate

Table 9. Test data				
Туре	e Input		Load	Test
	VI	t _r , t _f	CL	
74HC20-Q100	V _{CC}	6.0 ns	15 pF, 50 pF	t _{PLH} , t _{PHL}
74HCT20-Q100	3.0 V	6.0 ns	15 pF, 50 pF	t _{PLH} , t _{PHL}

Dual 4-input NAND gate

12. Package outline

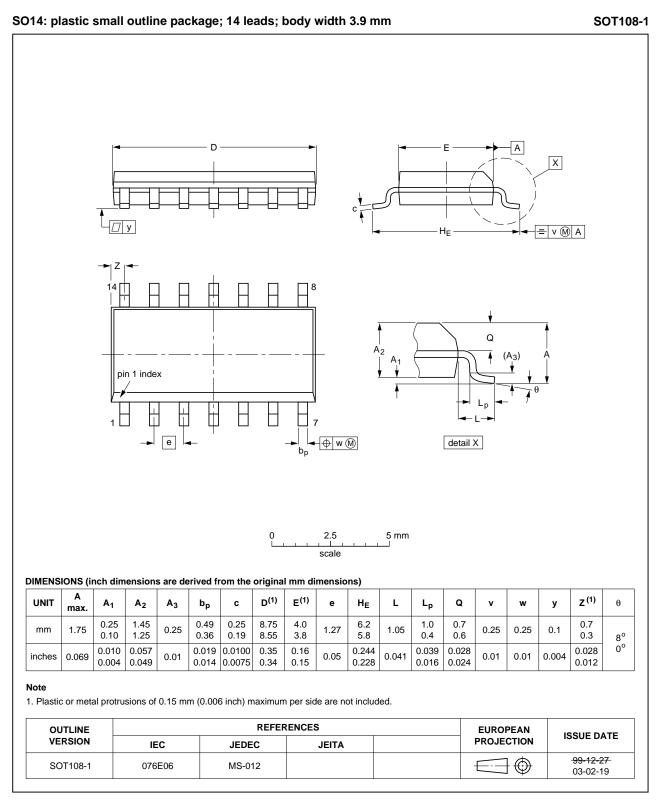


Fig 9. Package outline SOT108-1 (SO14)

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74HC_HCT20_Q100

Dual 4-input NAND gate

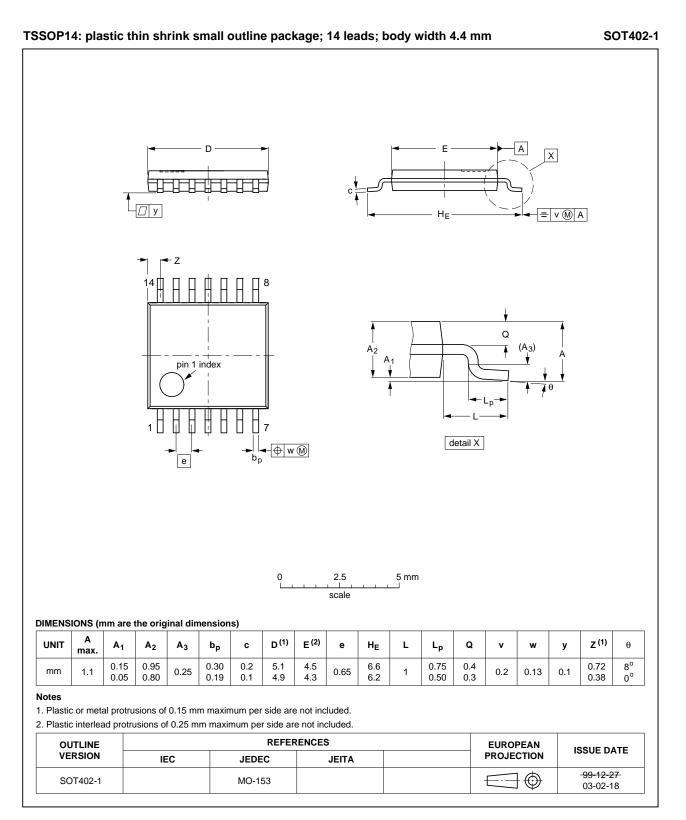


Fig 10. Package outline SOT402-1 (TSSOP14)

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74HC_HCT20_Q100

Dual 4-input NAND gate

13. Abbreviations

Table 10.	Abbreviations
Acronym	Description
CMOS	Complementary Metal Oxide Semiconductor
DUT	Device Under Test
ESD	ElectroStatic Discharge
HBM	Human Body Model
MM	Machine Model
TTL	Transistor-Transistor Logic
MIL	Military

14. Revision history

Table 11. Revision history					
Document ID	Release date	Data sheet status	Change notice	Supersedes	
74HC_HCT20_Q100 v.1	20120717	Product data sheet	-	-	

15. Legal information

15.1 Data sheet status

Document status[1][2]	Product status ^[3]	Definition
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Dual 4-input NAND gate

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Date of release: 17 July 2012 Document identifier: 74HC_HCT20_Q100

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